

ABSTRACT OF THE DISCLOSURE

A nonvolatile semiconductor memory device includes a plurality of blocks each having a memory cell array, a reference cell, a signal line that
5 supplies a reference signal read from the reference cell to each of the plurality of blocks, a reference load circuit which is provided in each of the plurality of blocks, and exerts a load on the reference signal that is identical to a load imposed
10 on data that is read from the memory cell array, and a sensing circuit which is provided in each of the plurality of blocks, and compares the data with the reference signal having the load imposed thereon by the reference load circuit so as to sense the data.